74AHC2G126; 74AHCT2G126

Dual buffer/line driver; 3-state

Rev. 04 — 27 April 2009 Product data sheet

1. General description

The 74AHC2G126 and 74AHCT2G126 are high-speed Si-gate CMOS devices. They provide a dual non-inverting buffer/line driver with 3-state output. The 3-state output is controlled by the output enable input (nOE). A LOW at nOE causes the output to assume a high-impedance OFF-state.

The AHC device has CMOS input switching levels and supply voltage range 2 V to 5.5 V.

The AHCT device has TTL input switching levels and supply voltage range 4.5 V to 5.5 V.

2. Features

- Symmetrical output impedance
- High noise immunity
- Low power dissipation
- Balanced propagation delays
- Multiple package options
- ESD protection:
  - HBM JESD22-A114E: exceeds 2000 V
  - MM JESD22-A115-A: exceeds 200 V
  - CDM JESD22-C101C: exceeds 1000 V
- Specified from –40 °C to +125 °C

3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74AHC2G126DP	–40 °C to +125 °C	TSSOP8	plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm	SOT505-2
74AHCT2G126DP				
74AHC2G126DC	–40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1
74AHCT2G126DC				
74AHC2G126GD	–40 °C to +125 °C	XSON8U	plastic extremely thin small outline package; no leads; 8 terminals; UTLP based; body 3 × 2 × 0.5 mm	SOT996-2
74AHCT2G126GD				

4. Marking

Table 2. Marking codes

Type number	Marking[1]
74AHC2G126DP	A26
74AHCT2G126DP	C26
74AHC2G126DC	A26
74AHCT2G126DC	C26
74AHC2G126GD	A26
74AHCT2G126GD	C26

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram

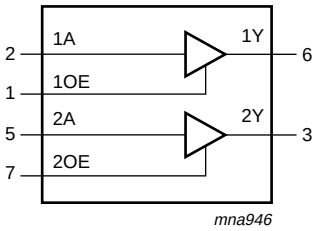


Fig 1. Logic symbol

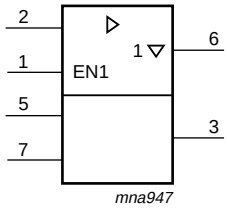


Fig 2. IEC logic symbol

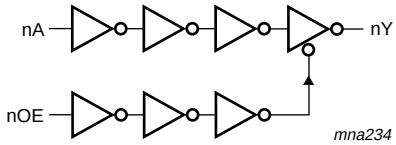


Fig 3. Logic diagram (one buffer)

6. Pinning information

6.1 Pinning

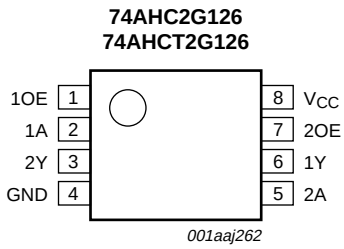
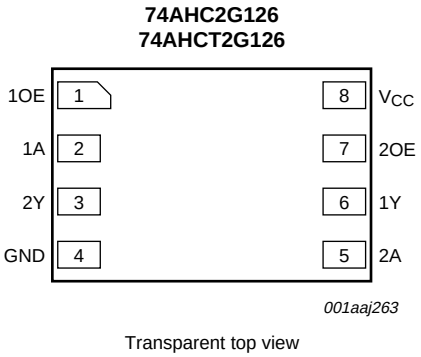


Fig 4. Pin configuration SOT505-2 (TSSOP8) and SOT765-1 (VSSOP8)



Transparent top view

Fig 5. Pin configuration SOT996-2 (XSON8U)

6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
1OE, 2OE	1, 7	output enable input (active LOW)
1A, 2A	2, 5	data input
GND	4	ground (0 V)
1Y, 2Y	6, 3	data output
V_{CC}	8	supply voltage

7. Functional description

Table 4. Function table[1]

Control	Input	Output
nOE	**nA**	**nY**
H	L	L
H	H	H
L	X	Z

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CC}	supply voltage			–0.5	+7.0	V
V_I	input voltage			–0.5	+7.0	V
I_{IK}	input clamping current	$V_I < –0.5$ V	[1]	–20	-	mA
I_{OK}	output clamping current	$V_O < –0.5$ V or $V_O > V_{CC} + 0.5$ V	[1]	-	±20	mA
I_O	output current	$–0.5 \text{ V} < V_O < V_{CC} + 0.5$ V		-	±25	mA
I_{CC}	supply current			-	75	mA
I_{GND}	ground current			–75	-	mA
T_{stg}	storage temperature			–65	+150	°C
P_{tot}	total power dissipation	T_{amb} = –40 °C to +125 °C	[2]	-	250	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For TSSOP8 package: above 55 °C the value of P_{tot} derates linearly with 2.5 mW/K.
For VSSOP8 package: above 110 °C the value of P_{tot} derates linearly with 8 mW/K.
For XSON8U package: above 118 °C the value of P_{tot} derates linearly with 7.8 mW/K.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	74AHC2G126			74AHCT2G126			Unit
			Min	Typ	Max	Min	Typ	Max	
V_{CC}	supply voltage		2.0	5.0	5.5	4.5	5.0	5.5	V
V_I	input voltage		0	-	5.5	0	-	5.5	V
V_O	output voltage		0	-	V_{CC}	0	-	V_{CC}	V
T_{amb}	ambient temperature		–40	+25	+125	–40	+25	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	V_{CC} = 3.3 V ± 0.3 V	-	-	100	-	-	-	ns/V
		V_{CC} = 5.0 V ± 0.5 V	-	-	20	-	-	20	ns/V

10. Static characteristics

Table 7. Static characteristics

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74AHC2G126										
V_{IH}	HIGH-level input voltage	V_{CC} = 2.0 V	1.5	-	-	1.5	-	1.5	-	V
		V_{CC} = 3.0 V	2.1	-	-	2.1	-	2.1	-	V
		V_{CC} = 5.5 V	3.85	-	-	3.85	-	3.85	-	V
V_{IL}	LOW-level input voltage	V_{CC} = 2.0 V	-	-	0.5	-	0.5	-	0.5	V
		V_{CC} = 3.0 V	-	-	0.9	-	0.9	-	0.9	V
		V_{CC} = 5.5 V	-	-	1.65	-	1.65	-	1.65	V
V_{OH}	HIGH-level output voltage	V_I = V_{IH} or V_{IL}								
		I_O = –50 µA; V_{CC} = 2.0 V	1.9	2.0	-	1.9	-	1.9	-	V
		I_O = –50 µA; V_{CC} = 3.0 V	2.9	3.0	-	2.9	-	2.9	-	V
		I_O = –50 µA; V_{CC} = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		I_O = –4.0 mA; V_{CC} = 3.0 V	2.58	-	-	2.48	-	2.40	-	V
		I_O = –8.0 mA; V_{CC} = 4.5 V	3.94	-	-	3.8	-	3.70	-	V
V_{OL}	LOW-level output voltage	V_I = V_{IH} or V_{IL}								
		I_O = 50 µA; V_{CC} = 2.0 V	-	0	0.1	-	0.1	-	0.1	V
		I_O = 50 µA; V_{CC} = 3.0 V	-	0	0.1	-	0.1	-	0.1	V
		I_O = 50 µA; V_{CC} = 4.5 V	-	0	0.1	-	0.1	-	0.1	V
		I_O = 4.0 mA; V_{CC} = 3.0 V	-	-	0.36	-	0.44	-	0.55	V
		I_O = 8.0 mA; V_{CC} = 4.5 V	-	-	0.36	-	0.44	-	0.55	V
I_{OZ}	OFF-state output current	V_I = V_{CC} or GND; V_{CC} = 5.5 V	-	-	0.25	-	2.5	-	10	µA
I_I	input leakage current	V_I = 5.5 V or GND; V_{CC} = 0 V to 5.5 V	-	-	0.1	-	1.0	-	2.0	µA
I_{CC}	supply current	V_I = V_{CC} or GND; I_O = 0 A; V_{CC} = 5.5 V	-	-	1.0	-	10	-	40	µA

Table 7. Static characteristics *…continued*

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
C_I	input capacitance		-	1.5	10	-	10	-	10	pF
74AHCT2G126										
V_{IH}	HIGH-level input voltage	V_{CC} = 4.5 V to 5.5 V	2.0	-	-	2.0	-	2.0	-	V
V_{IL}	LOW-level input voltage	V_{CC} = 4.5 V to 5.5 V	-	-	0.8	-	0.8	-	0.8	V
V_{OH}	HIGH-level output voltage	V_I = V_{IH} or V_{IL}; V_{CC} = 4.5 V								
		I_O = –50 µA	4.4	4.5	-	4.4	-	4.4	-	V
		I_O = –8.0 mA	3.94	-	-	3.8	-	3.70	-	V
V_{OL}	LOW-level output voltage	V_I = V_{IH} or V_{IL}; V_{CC} = 4.5 V								
		I_O = 50 µA	-	0	0.1	-	0.1	-	0.1	V
		I_O = 8.0 mA	-	-	0.36	-	0.44	-	0.55	V
I_{OZ}	OFF-state output current	V_I = V_{CC} or GND; V_{CC} = 5.5 V	-	-	0.25	-	2.5	-	10	µA
I_I	input leakage current	V_I = 5.5 V or GND; V_{CC} = 0 V to 5.5 V	-	-	0.1	-	1.0	-	2.0	µA
I_{CC}	supply current	V_I = V_{CC} or GND; I_O = 0 A; V_{CC} = 5.5 V	-	-	1.0	-	10	-	40	µA
ΔI_{CC}	additional supply current	per input pin; V_I = 3.4 V; other inputs at V_{CC} or GND; I_O = 0 A; V_{CC} = 5.5 V	-	-	1.35	-	1.5	-	1.5	mA
C_I	input capacitance		-	1.5	10	-	10	-	10	pF

11. Dynamic characteristics

Table 8. Dynamic characteristics

GND = 0 V; for test circuit see Figure 8.

Symbol	Parameter	Conditions		25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
74AHC2G126											
t_{pd}	propagation delay	nA to nY; see Figure 6	[1]								
		V_{CC} = 3.0 V to 3.6 V	[2]								
		C_L = 15 pF		-	4.7	8.0	1.0	9.5	1.0	11.5	ns
		C_L = 50 pF		-	6.6	11.5	1.0	13.0	1.0	14.5	ns
		V_{CC} = 4.5 V to 5.5 V	[3]								
		C_L = 15 pF		-	3.4	5.5	1.0	6.5	1.0	7.0	ns
		C_L = 50 pF		-	4.8	7.5	1.0	8.5	1.0	9.5	ns

Table 8. Dynamic characteristics *…continued*

GND = 0 V; for test circuit see Figure 8.

Symbol	Parameter	Conditions		25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
t_{en}	enable time	nOE to nY; see Figure 7	[1]								
		V_{CC} = 3.0 V to 3.6 V	[2]								
		C_L = 15 pF		-	5.0	8.0	1.0	9.5	1.0	11.5	ns
		C_L = 50 pF		-	6.9	11.5	1.0	13.0	1.0	14.5	ns
		V_{CC} = 4.5 V to 5.5 V	[3]								
		C_L = 15 pF		-	3.6	5.1	1.0	6.0	1.0	6.5	ns
		C_L = 50 pF		-	4.9	7.5	1.0	9.0	1.0	9.5	ns
t_{dis}	disable time	nOE to nY; see Figure 7	[1]								
		V_{CC} = 3.0 V to 3.6 V	[2]								
		C_L = 15 pF		-	6.0	9.7	1.0	11.5	1.0	12.5	ns
		C_L = 50 pF		-	8.3	13.2	1.0	15.0	1.0	16.5	ns
		V_{CC} = 4.5 V to 5.5 V	[3]								
		C_L = 15 pF		-	4.1	6.8	1.0	8.0	1.0	8.5	ns
		C_L = 50 pF		-	5.7	8.8	1.0	10.0	1.0	11.0	ns
C_{PD}	power dissipation capacitance	per buffer; C_L = 50 pF; f_i = 1 MHz; V_I = GND to V_{CC}	[4]	-	10	-	-	-	-	-	pF
74AHCT2G126											
t_{pd}	propagation delay	nA to nY; see Figure 6	[1]								
		V_{CC} = 4.5 V to 5.5 V	[3]								
		C_L = 15 pF		-	3.4	5.5	1.0	6.5	1.0	7.0	ns
		C_L = 50 pF		-	4.8	7.5	1.0	8.5	1.0	9.5	ns
t_{en}	enable time	nOE to nY; see Figure 7	[1]								
		V_{CC} = 4.5 V to 5.5 V	[3]								
		C_L = 15 pF		-	3.9	5.1	1.0	6.0	1.0	6.5	ns
		C_L = 50 pF		-	5.1	7.5	1.0	9.0	1.0	9.5	ns
t_{dis}	disable time	nOE to nY; see Figure 7	[1]								
		V_{CC} = 4.5 V to 5.5 V	[3]								
		C_L = 15 pF		-	4.5	6.8	1.0	8.0	1.0	8.5	ns
		C_L = 50 pF		-	6.1	8.8	1.0	10.0	1.0	11.0	ns

Table 8. Dynamic characteristics *…continued*

GND = 0 V; for test circuit see Figure 8.

Symbol	Parameter	Conditions		25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
C_{PD}	power dissipation capacitance	per buffer; C_L = 50 pF; f_i = 1 MHz; V_I = GND to V_{CC}	[4]	-	10	-	-	-	-	-	pF

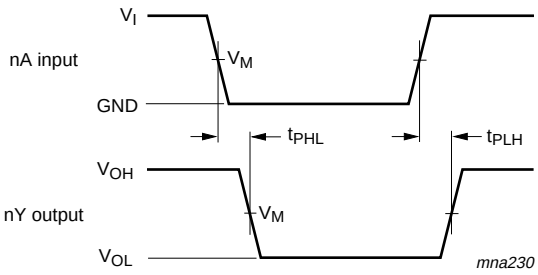
[1] t_{pd} is the same as t_{PLH} and t_{PHL}.
t_{en} is the same as t_{PZL} and t_{PZH}.
t_{dis} is the same as t_{PLZ} and t_{PHZ}.

[2] Typical values are measured at V_{CC} = 3.3 V.

[3] Typical values are measured at V_{CC} = 5.0 V.

[4] C_{PD} is used to determine the dynamic power dissipation P_D (µW).
$P_D = C_{PD} \times V_{CC}^2 \times f_i + \sum (C_L \times V_{CC}^2 \times f_o)$ where:
f_i = input frequency in MHz;
f_o = output frequency in MHz;
C_L = output load capacitance in pF;
V_{CC} = supply voltage in Volts.

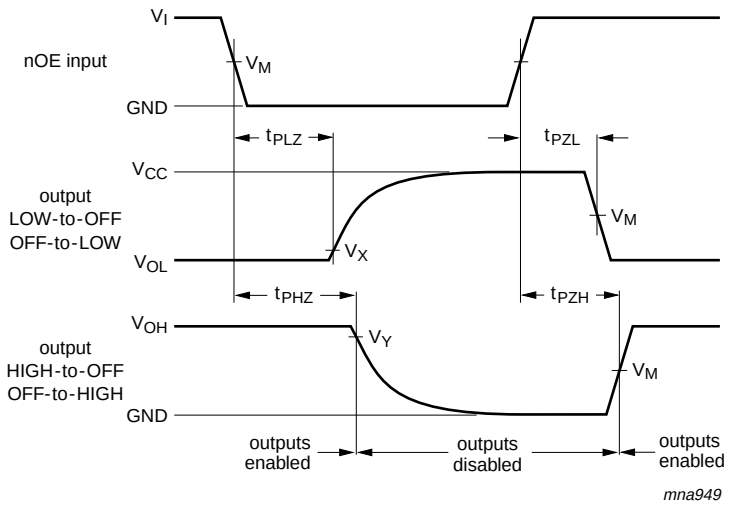
12. Waveforms



Measurement points are given in Table 9.

Logic levels: V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 6. Input (nA) to output (nY) propagation delays



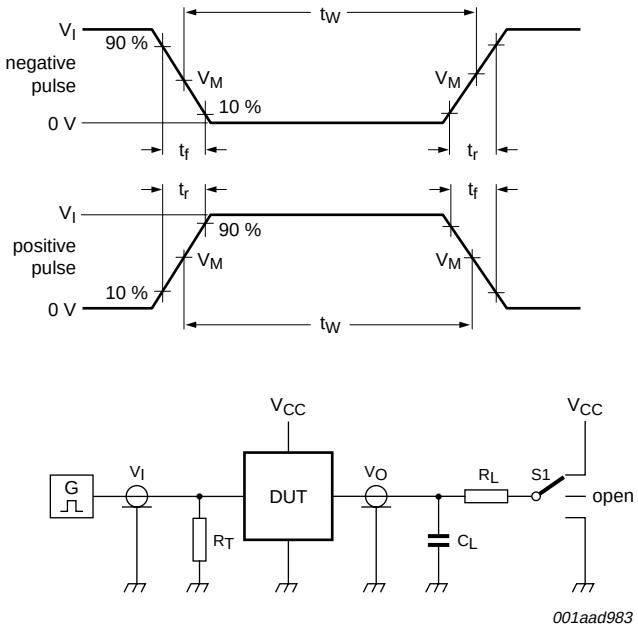
Measurement points are given in Table 9.

Logic levels: V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 7. Enable and disable times

Table 9. Measurement points

Type	Input	Output		
	V_M	V_M	V_X	V_Y
74AHC2G126	$0.5V_{CC}$	$0.5V_{CC}$	V_{OL} + 0.3 V	V_{OH} − 0.3 V
74AHCT2G126	1.5 V	$0.5V_{CC}$	V_{OL} + 0.3 V	V_{OH} − 0.3 V



Test data is given in Table 10.

Definitions test circuit:

R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

C_L = Load capacitance including jig and probe capacitance.

R_L = Load resistance.

S1 = Test selection switch.

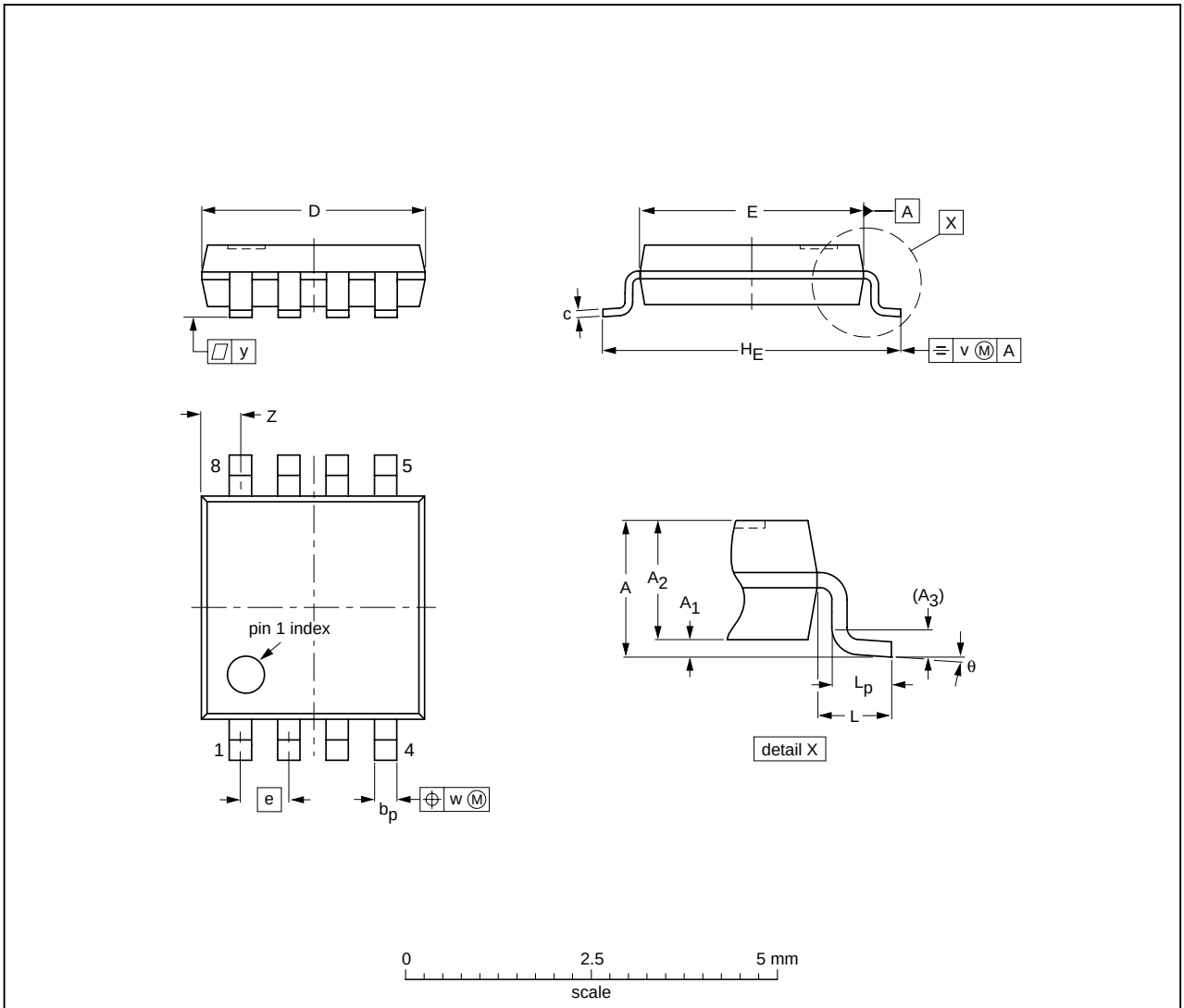
Fig 8. Test circuit for measuring switching times

Table 10. Test data

Type	Input		Load		S1 position		
	V_I	t_r, t_f	C_L	R_L	t_{PHL}, t_{PLH}	t_{PZH}, t_{PHZ}	t_{PZL}, t_{PLZ}
74AHC2G126	V_{CC}	≤ 3 ns	15 pF, 50 pF	1 kΩ	open	GND	V_{CC}
74AHCT2G126	3 V	≤ 3 ns	15 pF, 50 pF	1 kΩ	open	GND	V_{CC}

13. Package outline

TSSOP8: plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm SOT505-2



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	$D^{(1)}$	$E^{(1)}$	e	H_E	L	L_p	v	w	y	$Z^{(1)}$	θ
mm	1.1	0.15 0.00	0.95 0.75	0.25	0.38 0.22	0.18 0.08	3.1 2.9	3.1 2.9	0.65	4.1 3.9	0.5	0.47 0.33	0.2	0.13	0.1	0.70 0.35	8° 0°

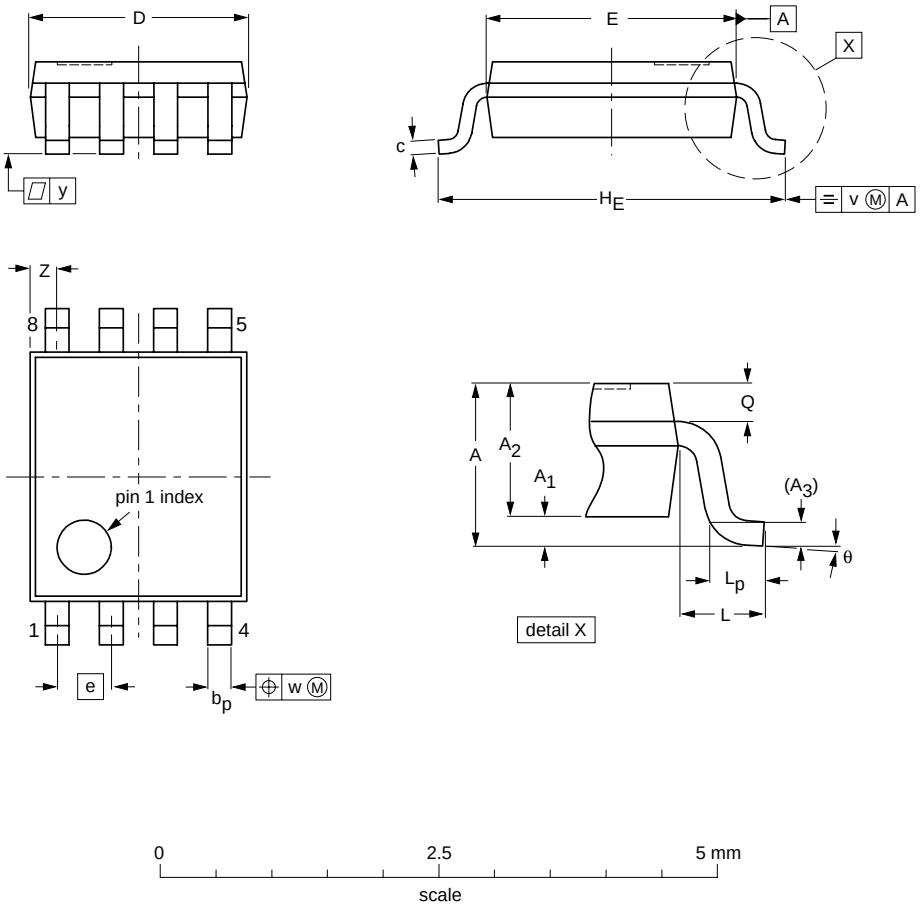
Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT505-2		- - -				02-01-16

Fig 9. Package outline SOT505-2 (TSSOP8)

VSSOP8: plastic very thin shrink small outline package; 8 leads; body width 2.3 mm **SOT765-1**



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	$D^{(1)}$	$E^{(2)}$	e	H_E	L	L_p	Q	v	w	y	$Z^{(1)}$	θ
mm	1	0.15 0.00	0.85 0.60	0.12	0.27 0.17	0.23 0.08	2.1 1.9	2.4 2.2	0.5	3.2 3.0	0.4	0.40 0.15	0.21 0.19	0.2	0.13	0.1	0.4 0.1	8° 0°

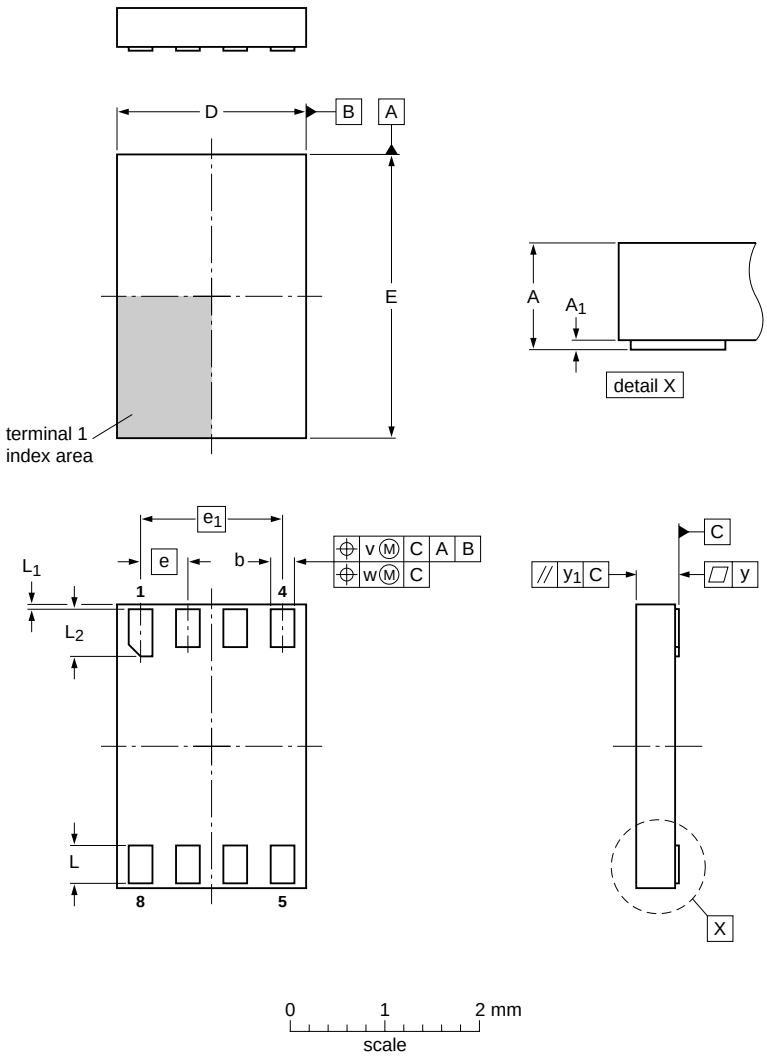
Notes

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
2. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT765-1		MO-187				02-06-07

Fig 10. Package outline SOT765-1 (VSSOP8)

XSON8U: plastic extremely thin small outline package; no leads; 8 terminals; UTLP based; body 3 x 2 x 0.5 mm **SOT996-2**



DIMENSIONS (mm are the original dimensions)

UNIT	A max	A_1	b	D	E	e	e_1	L	L_1	L_2	v	w	y	y_1
mm	0.5	0.05 0.00	0.35 0.15	2.1 1.9	3.1 2.9	0.5	1.5	0.5 0.3	0.15 0.05	0.6 0.4	0.1	0.05	0.05	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT996-2	- - -		- - -			~~07-12-18~~ 07-12-21

Fig 11. Package outline SOT996-2 (XSON8U)

14. Abbreviations

Table 11. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

15. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AHC_AHCT2G126_4	20090427	Product data sheet	-	74AHC_AHCT2G126_3
Modifications:	• Table 5: the total power dissipation value for XSON8U has been changed.			
74AHC_AHCT2G126_3	20090115	Product data sheet	-	74AHC_AHCT2G126_2
74AHC_AHCT2G126_2	20040921	Product data sheet	-	74AHC_AHCT2G126_1
74AHC_AHCT2G126_1	20040113	Product specification	-	-

16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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18. Contents

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